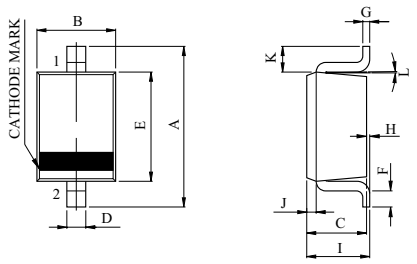
KDV1472

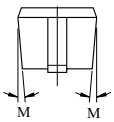
VARIABLE CAPACITANCE DIODE
SILICON EPITAXIAL PLANAR DIODE

FM RADIO BAND TUNING APPLICATION.

FEATURES

- High Capacitance Ratio : C_{1V}/C_{5V}=5.0(Min.)
- Excellent C-V Characteristics.
- Variations of Capacitance Values is Little.
- Small Package.





1. ANODE
2. CATHODE

DIM	MILLIMETERS
A	2.50±0.1
B	1.25±0.05
C	0.90±0.05
D	0.30+0.06/-0.04
E	1.70±0.05
F	MIN 0.17
G	0.126±0.03
H	0~0.1
I	1.0 MAX
J	0.15±0.05
K	0.4±0.05
L	2°+4/-2
M	4~6°

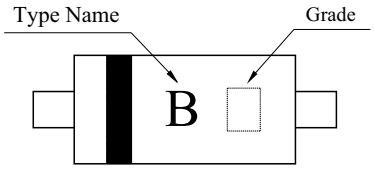
USC

MAXIMUM RATING (Ta=25℃)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Reverse Voltage	V_R	16	V
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	-55～150	℃

GRADE	CAPACITANCE(C_{IV})	UNIT
A	30.16~33.63	pF
B	33.30~37.13	
C	36.77~40.99	

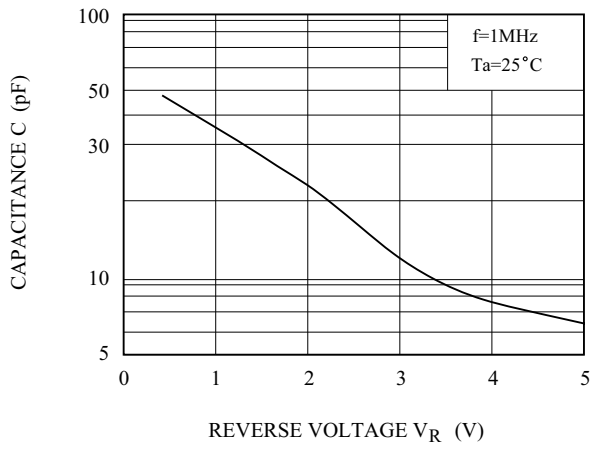
Marking



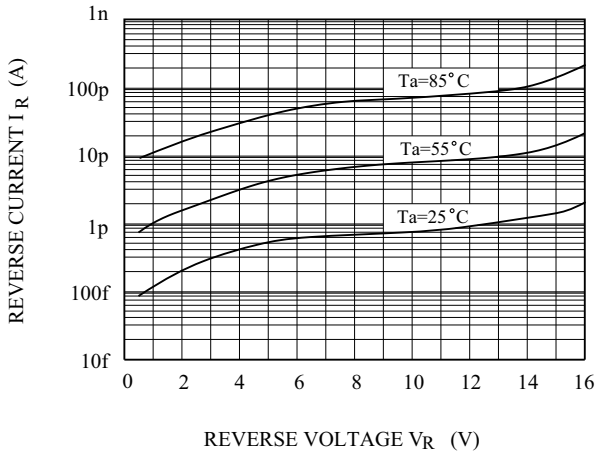
ELECTRICAL CHARACTERISTICS (Ta=25℃)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Reverse Voltage	V_R	I_R=10㎂	16	-	-	V
Reverse Current	I_R	V_R=10V	-	-	50	nA
Capacitance	C_{1V}	V_R=1V, f=1MHz	30.16	35.60	40.99	pF
	$C_{4.5V}$	V_R=4.5V, f=1MHz	6.2	7.7	9.2	
Capacitance Ratio	K	C_{1V}/C_{5V}, f=1MHz	5.0	-	-	
Series Resistance	r_S	V_R=1.5V, f=100MHz	-	0.8	1.0	Ω

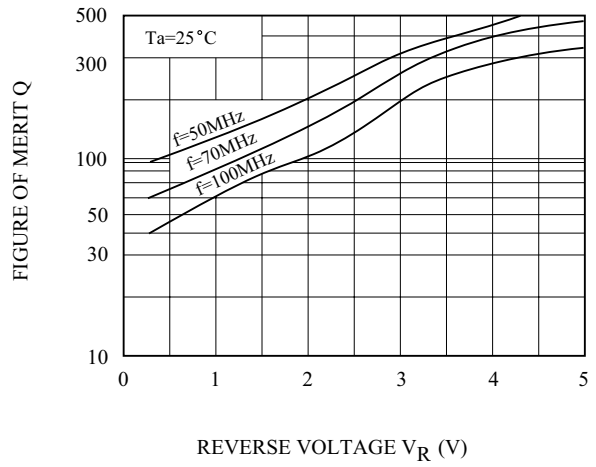
C - V_R



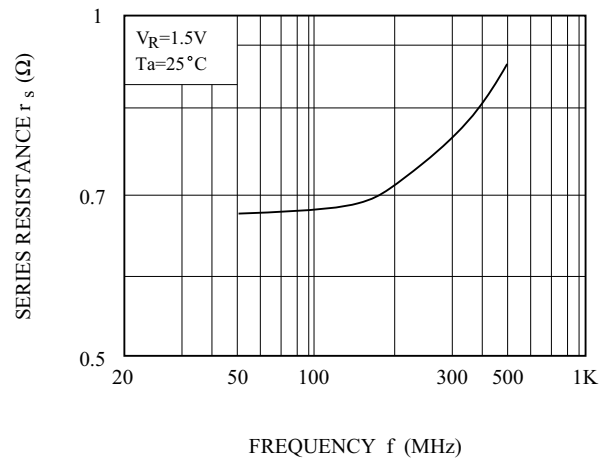
I_R - V_R



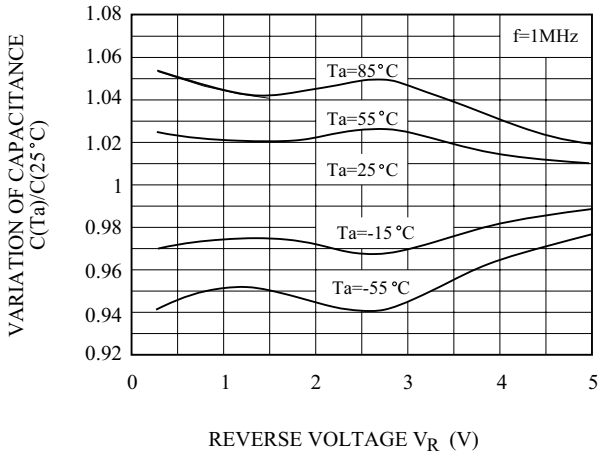
Q_R - V



r_s - f



C(Ta)/C(25°C) - V_R (V)



(ppm/° C) - V_R